FUJITSU SEMICONDUCTOR
DATA SHEET

DS501-00016-2v0-E

Memory FRAM

4 K (512 × 8) Bit I²C

MB85RC04V

■ DESCRIPTION

The MB85RC04V is an FRAM (Ferroelectric Random Access Memory) chip in a configuration of 512 words × 8 bits, using the ferroelectric process and silicon gate CMOS process technologies for forming the nonvolatile memory cells.

Unlike SRAM, the MB85RC04V is able to retain data without using a data backup battery.

The read/write endurance of the nonvolatile memory cells used for the MB85RC04V has improved to be at least 10^{12} cycles, significantly outperforming other nonvolatile memory products in the number.

The MB85RC04V does not need a polling sequence after writing to the memory such as the case of Flash memory or E²PROM.

■ FEATURES

- Bit configuration : 512 words × 8 bits
- Two-wire serial interface : Fully controllable by two ports: serial clock (SCL) and serial data (SDA).
- Operating frequency : 1 MHz (Max)
- Read/write endurance : 10^{12} times / byte
- Data retention : 10 years (+ 85 °C), 95 years (+ 55 °C), over 200 years (+ 35 °C)
- Operating power supply voltage : 3.0 V to 5.5 V
- Low-power consumption : Operating power supply current 90 µA (Typ @1 MHz)
  Standby current 5 µA (Typ)
- Operation ambient temperature range
  : − 40 °C to + 85 °C
- Package : 8-pin plastic SOP (FPT-8P-M02)
  RoHS compliant

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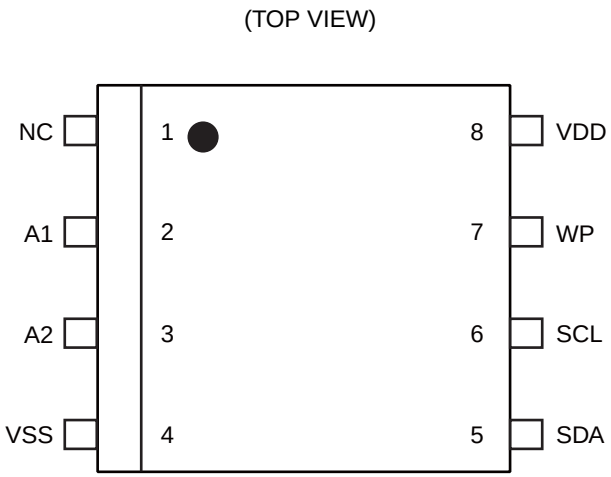
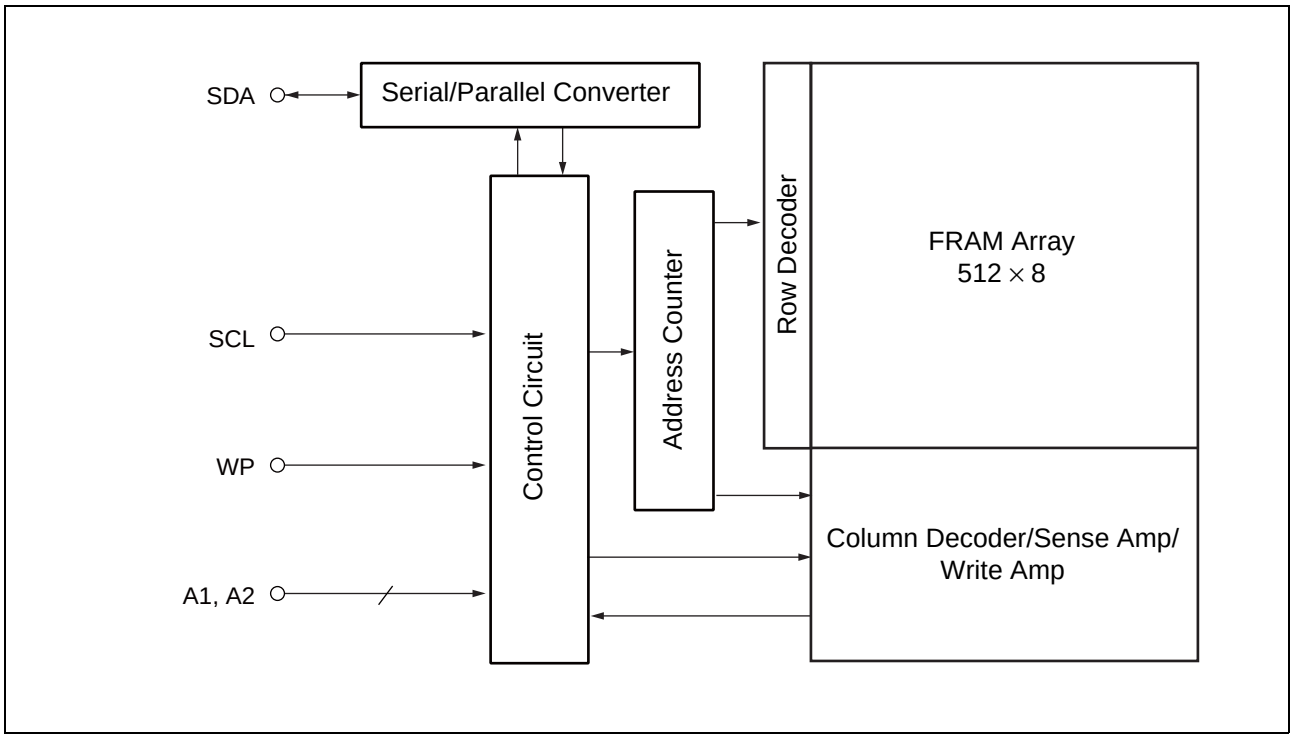
■ PIN ASSIGNMENT



■ PIN FUNCTIONAL DESCRIPTIONS

Pin Number	Pin Name	Functional Description
1	NC	No Connect pin Leave this pin open, or connect to VDD or VSS.
2, 3	A1, A2	Device Address pins The MB85RC04V can be connected to the same data bus up to 4 devices. Device addresses are used in order to identify each of these devices. Connect these pins to VDD pin or VSS pin externally. Only if the combination of VDD and VSS pins matches Device Address Code inputted from the SDA pin, the device operates. In the open pin state, A1 and A2 pins are internally pulled-down and recognized as the "L" level.
4	VSS	Ground pin
5	SDA	Serial Data I/O pin This is an I/O pin which performs bidirectional communication for both memory address and writing/reading data. It is possible to connect multiple devices. It is an open drain output, so a pull-up resistor is required to be connected to the external circuit.
6	SCL	Serial Clock pin This is a clock input pin for input/output timing serial data. Data is sampled on the rising edge of the clock and output on the falling edge.
7	WP	Write Protect pin When the Write Protect pin is the “H” level, the writing operation is disabled. When the Write Protect pin is the “L” level, the entire memory region can be overwritten. The reading operation is always enabled regardless of the Write Protect pin input level. The write protect pin is internally pulled down to VSS pin, and that is recognized as the “L” level (write enabled) when the pin is the open state.
8	VDD	Supply Voltage pin

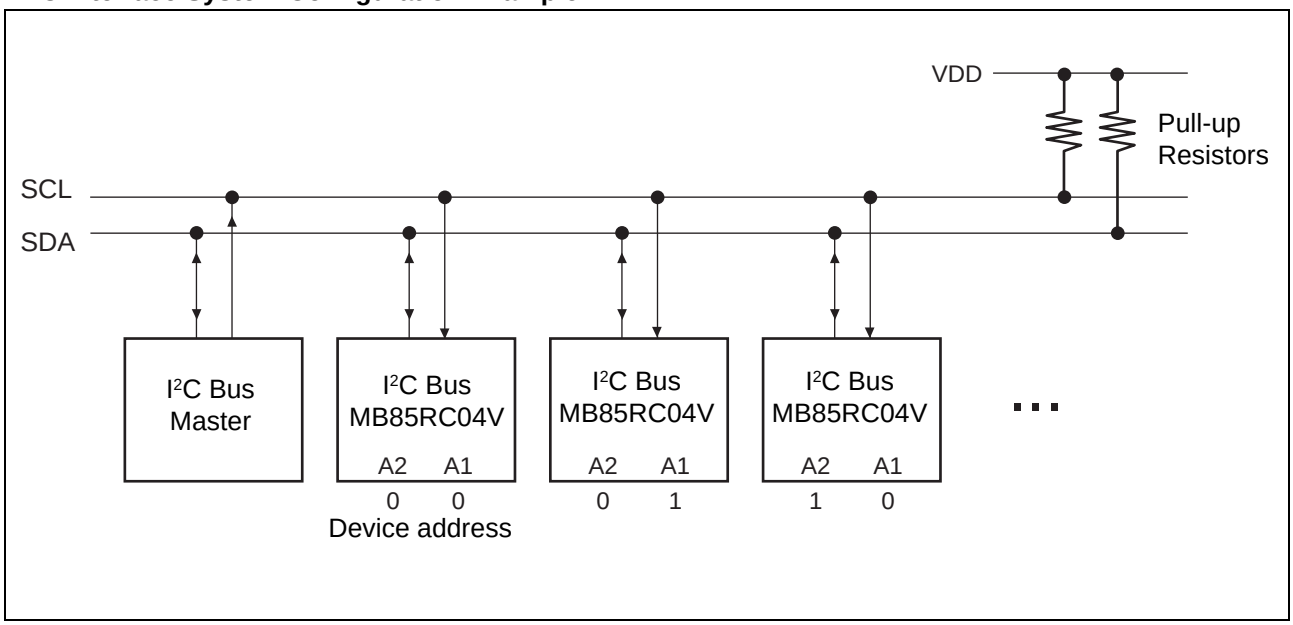
■ BLOCK DIAGRAM



■ I²C (Inter-Integrated Circuit)

The MB85RC04V has the two-wire serial interface; the I²C bus,and operates as a slave device.
The I²C bus defines communication roles of “master” and “slave” devices, with the master side holding the authority to initiate control. Furthermore, the I²C bus connection is possible where a single master device is connected to multiple slave devices in a party-line configuration. In this case, it is necessary to assign a unique device address to the slave device, the master side starts communication after specifying the slave to communicate by addresses.

• I²C Interface System Configuration Example



■ I²C COMMUNICATION PROTOCOL

The I²C bus is a two wire serial interface that uses a bidirectional data bus (SDA) and serial clock (SCL). A data transfer can only be initiated by the master, which will also provide the serial clock for synchronization. The SDA signal should change while SCL is the “L” level. However, as an exception, when starting and stopping communication sequence, SDA is allowed to change while SCL is the “H” level.

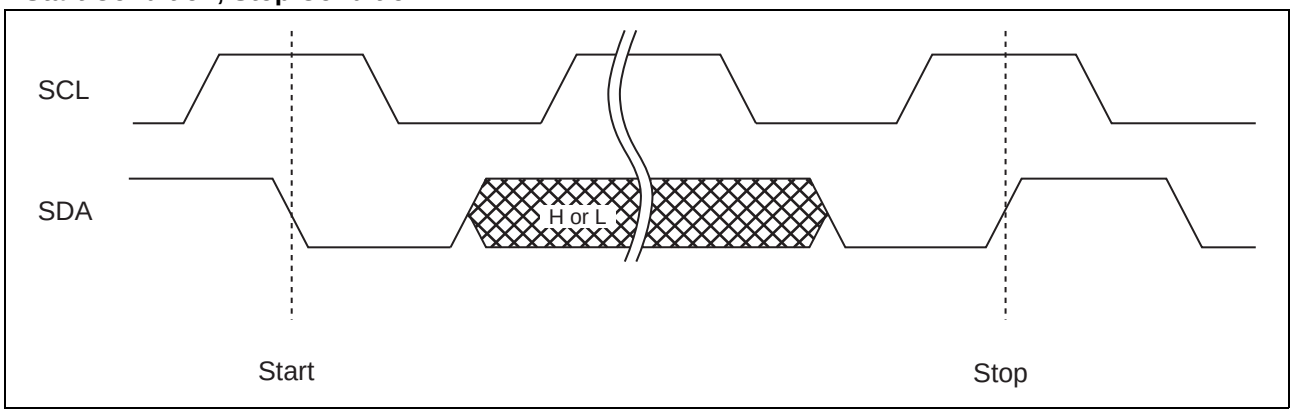
- Start Condition

To start read or write operations by the I²C bus, change the SDA input from the “H” level to the “L” level while the SCL input is in the “H” level.

- Stop Condition

To stop the I²C bus communication, change the SDA input from the “L” level to the “H” level while the SCL input is in the “H” level. In the reading operation, inputting the stop condition finishes reading and enters the standby state. In the writing operation, inputting the stop condition finishes inputting the rewrite data and enters the standby state.

• Start Condition, Stop Condition



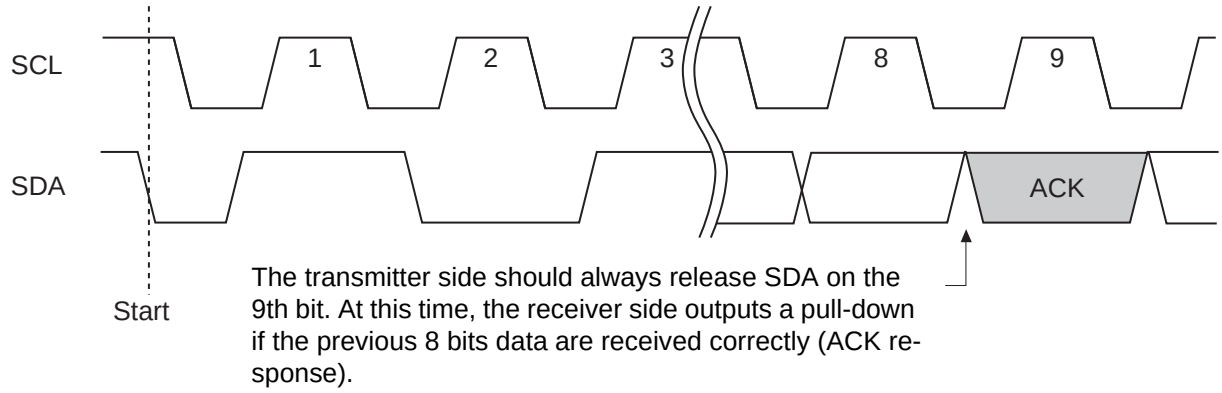
Note : At the write operation, the FRAM device does not need the programming wait time (t_{WC}) after issuing the Stop Condition.

■ ACKNOWLEDGE (ACK)

In the I²C bus, serial data including address or memory information is sent in units of 8 bits. The acknowledge signal indicates that every 8 bits of the data is successfully sent and received. The receiver side usually outputs the “L” level every time on the 9th SCL clock after each 8 bits are successfully transmitted and received. On the transmitter side, the bus is temporarily released to Hi-Z every time on this 9th clock to allow the acknowledge signal to be received and checked. During this Hi-Z released period, the receiver side pulls the SDA line down to indicate the “L” level that the previous 8 bits communication is successfully received.

In case the slave side receives Stop condition before sending or receiving the ACK “L” level, the slave side stops the operation and enters to the standby state. On the other hand, the slave side releases the bus state after sending or receiving the NACK “H” level. The master side generates Stop condition or Start condition in this released bus state.

• **Acknowledge timing overview diagram**



■ MEMORY ADDRESS STRUCTURE

The MB85RC04V has the memory address buffer to store the 9-bit information for the memory address.

As for byte write, page write and random read commands, the complete 9-bit memory address is configured by inputting the memory upper address (1 bit) and the memory lower address (8 bits), and saved to the memory address buffer. Then access to the memory is performed.

As for a current address read command, the complete 9-bit memory address is configured and saved to the memory address buffer, by inputting the memory upper address (1 bit) and the memory lower address (8 bits) which has saved in the memory address buffer. Then access to the memory is performed.

■ DEVICE ADDRESS WORD

Following the start condition, the 8 bit device address word is input. Inputting the device address word decides whether writing or reading operation. However, the clock is always driven by the master. The device address word (8 bits) consists of a device Type code (4 bits), device address code (2 bits), memory upper address code (1 bit), and a Read/Write code (1 bit).

- Device Type Code (4 bits)

The upper 4 bits of the device address word are a device type code that identifies the device type, and are fixed at “1010” for the MB85RC04V.

- Device Address Code (2 bits): A1, A2

Following the device type code, the 2 bits of the device address code are input in order of A2 and A1.

The device address code identifies one device from up to 4 devices connected to the bus.

Each MB85RC04V is given a unique 2 bits code on the device address pin (external hardware pin A2 and A1). The slave only responds if the received device address code is equal to this unique 2 bits code.

- Memory Upper Address Code (1 bit): A8

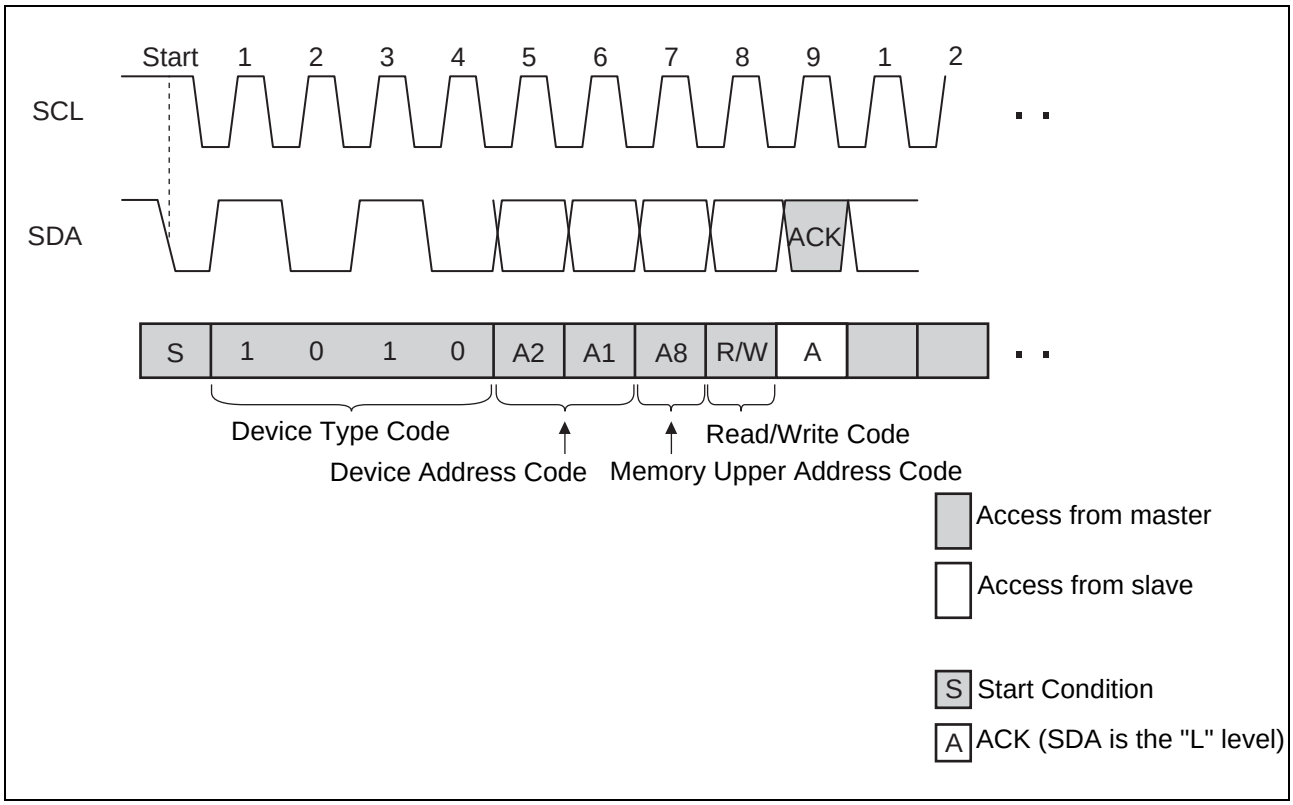
Following the device address code, the 1-bit memory upper address code are input.

This bit is not the setting bit for the slave address, but the upper 1-bit setting bit for the memory address.

- Read/Write Code (1 bit)

The 8th bit of the device address word is the R/W (Read/Write) code. When the R/W code is “0” input, a write operation is enabled, and the R/W code is “1” input, a read operation is enabled for the MB85RC04V. If the device type code is not “1010” or the device address code is not equal to the setting of the external device address pins, the Read/Write operation is not performed and the standby state is chosen.

• Device Address Word



■ DATA STRUCTURE

The master inputs the device address word (8 bits) following the start condition, and then the slave outputs the Acknowledge “L” level on the 9th bit. After confirming the Acknowledge response, the sequential 8-bit memory lower address is input, to the byte write, page write and random read commands.

As for the current address read command, inputting the memory lower address is not performed, and the address buffer lower 8-bit is used as the memory lower address.

When inputting the memory lower address finishes, the slave outputs the Acknowledge “L” level on the 9th bit again.

Afterwards, the input and the output data continue in 8-bit units, and then the Acknowledge “L” level is output for every 8-bit data.

■ FRAM ACKNOWLEDGE -- POLLING NOT REQUIRED

The MB85RC04V performs the high speed write operations, so any waiting time for an ACK* by the acknowledge polling does not occur.

*: In E^2PROM, the Acknowledge Polling is performed as a progress check whether rewriting is executed or not. It is normal to judge by the 9th bit of Acknowledge whether rewriting is performed or not after inputting the start condition and then the device address word (8 bits) during rewriting.

■ WRITE PROTECT (WP)

The entire memory array can be write protected by setting the WP pin to the “H” level. When the WP pin is set to the “L” level, the entire memory array will be rewritten. Reading is allowed regardless of the WP pin's “H” level or “L” level.

Do not change the WP signal level during the communication period from the start condition to the stop condition.

Note : The WP pin is pulled down internally to the VSS pin, therefore if the WP pin is open, the pin status is recognized as the “L” level (write enabled).

■ ELECTRICAL CHARACTERISTICS

1. DC Characteristics

(within recommended operating conditions)

Parameter	Symbol	Condition	Value			Unit
			Min	Typ	Max	
Input leakage current*1	$\|I_{LI}\|$	V_{IN} = 0 V to V_{DD}	—	—	1	µA
Output leakage current*2	$\|I_{LO}\|$	V_{OUT} = 0 V to V_{DD}	—	—	1	µA
Operating power supply current	I_{DD}	SCL = 400 kHz	—	40	80	µA
		SCL = 1000 kHz	—	90	130	µA
Standby current	I_{SB}	SCL, SDA = V_{DD} WP = 0 V or V_{DD} or Open Under Stop Condition T_A = + 25 °C	—	5	10	µA
“L” level output voltage	V_{OL}	I_{OL} = 3 mA	—	—	0.4	V
Input resistance for WP, A1, and A2 pins	R_{IN}	V_{IN} = V_{IL} (Max)	50	—	—	kΩ
		V_{IN} = V_{IH} (Min)	1	—	—	MΩ

*1: Applicable pin: SCL,SDA

*2: Applicable pin: SDA

2. AC Characteristics

Parameter	Symbol	Value						Unit
		STANDARD MODE		FAST MODE		FAST MODE PLUS		
		Min	Max	Min	Max	Min	Max	
SCL clock frequency	FSCL	0	100	0	400	0	1000	kHz
Clock high time	T_{HIGH}	4000	—	600	—	400	—	ns
Clock low time	T_{LOW}	4700	—	1300	—	600	—	ns
SCL/SDA rising time	T_r	—	1000	—	300	—	300	ns
SCL/SDA falling time	T_f	—	300	—	300	—	100	ns
Start condition hold	$T_{HD:STA}$	4000	—	600	—	250	—	ns
Start condition setup	$T_{SU:STA}$	4700	—	600	—	250	—	ns
SDA input hold	$T_{HD:DAT}$	0	—	0	—	0	—	ns
SDA input setup	$T_{SU:DAT}$	250	—	100	—	100	—	ns
SDA output hold	$T_{DH:DAT}$	0	—	0	—	0	—	ns
Stop condition setup	$T_{SU:STO}$	4000	—	600	—	250	—	ns
SDA output access after SCL falling	T_{AA}	—	3000	—	900	—	550	ns
Pre-charge time	T_{BUF}	4700	—	1300	—	500	—	ns
Noise suppression time (SCL and SDA)	T_{SP}	—	50	—	50	—	50	ns

AC characteristics were measured under the following measurement conditions.

- Power supply voltage : STANDARD MODE and FAST MODE 3.0 V to 5.5 V
  : FAST MODE PLUS 4.5 V to 5.5 V
- Operation ambient temperature : – 40 °C to + 85 °C
- Input voltage magnitude : $V_{DD} \times 0.2$ to $V_{DD} \times 0.8$
- Input rising time : 5 ns
- Input falling time : 5 ns
- Input judge level : $V_{DD}/2$
- Output judge level : $V_{DD}/2$

2. AC Characteristics

Parameter	Symbol	Value						Unit
		STANDARD MODE		FAST MODE		FAST MODE PLUS		
		Min	Max	Min	Max	Min	Max	
SCL clock frequency	FSCL	0	100	0	400	0	1000	kHz
Clock high time	T_{HIGH}	4000	—	600	—	400	—	ns
Clock low time	T_{LOW}	4700	—	1300	—	600	—	ns
SCL/SDA rising time	T_r	—	1000	—	300	—	300	ns
SCL/SDA falling time	T_f	—	300	—	300	—	100	ns
Start condition hold	$T_{HD:STA}$	4000	—	600	—	250	—	ns
Start condition setup	$T_{SU:STA}$	4700	—	600	—	250	—	ns
SDA input hold	$T_{HD:DAT}$	0	—	0	—	0	—	ns
SDA input setup	$T_{SU:DAT}$	250	—	100	—	100	—	ns
SDA output hold	$T_{DH:DAT}$	0	—	0	—	0	—	ns
Stop condition setup	$T_{SU:STO}$	4000	—	600	—	250	—	ns
SDA output access after SCL falling	T_{AA}	—	3000	—	900	—	550	ns
Pre-charge time	T_{BUF}	4700	—	1300	—	500	—	ns
Noise suppression time (SCL and SDA)	T_{SP}	—	50	—	50	—	50	ns

AC characteristics were measured under the following measurement conditions.

- Power supply voltage : STANDARD MODE and FAST MODE 3.0 V to 5.5 V
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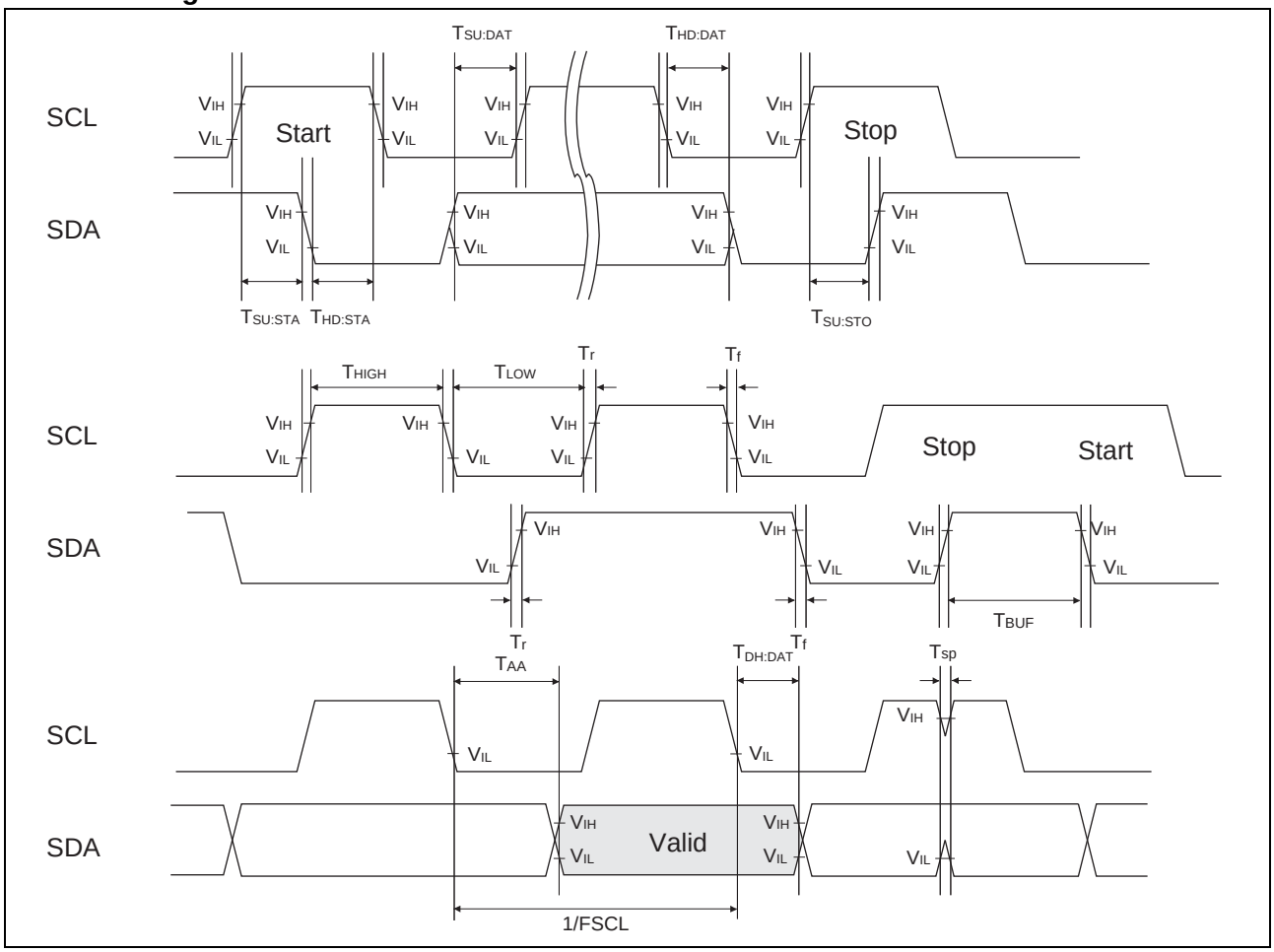
- Output judge level : $V_{DD}/2$

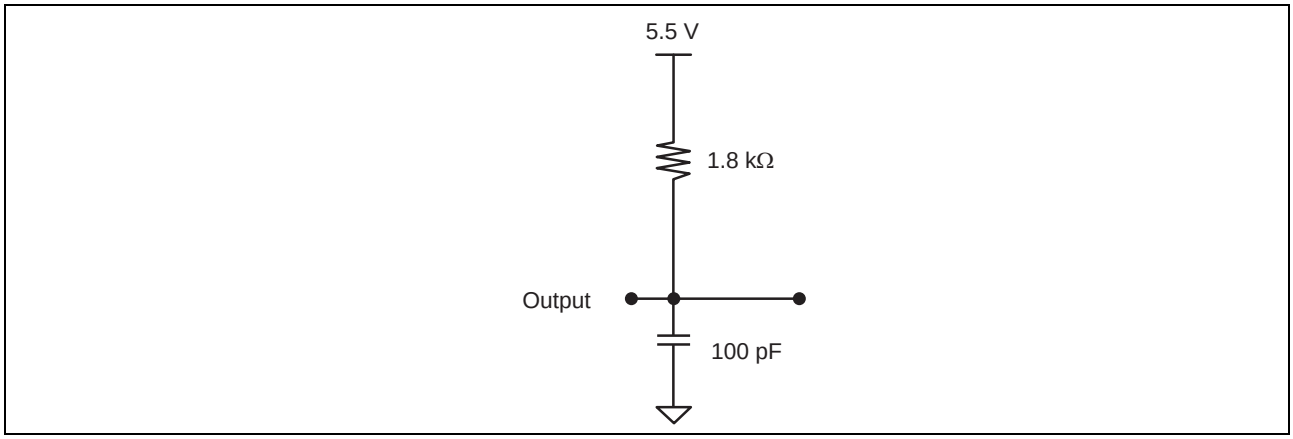
3. AC Timing Definitions



4. Pin Capacitance

Parameter	Symbol	Conditions	Value			Unit
			Min	Typ	Max	
I/O capacitance	$C_{I/O}$	$V_{DD} = V_{IN} = V_{OUT} = 0$ V, f = 1 MHz, T_A = + 25 °C	—	—	15	pF
Input capacitance	C_{IN}		—	—	15	pF

5. AC Test Load Circuit



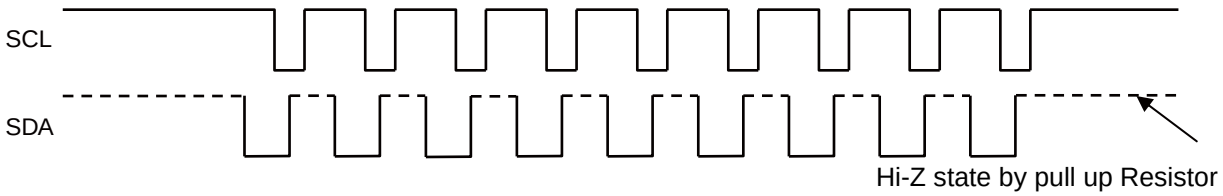
■ SOFTWARE RESET SEQUENCE OR COMMAND RETRY

In case the malfunction has occurred after power on, the master side stopped the I²C communication during processing, or unexpected malfunction has occurred, execute the following (1) software recovery sequence just before each command, or (2) retry command just after failure of each command.

(1) Software Reset Sequence

Since the slave side may be outputting “L” level, do not force to drive “H” level, when the master side drives the SDA port. This is for preventing a bus conflict. The additional hardware is not necessary for this software reset sequence.

9 set of “Start Conditions and one “1” data”



Send “Start Condition and one data “1”” .
Repeat these 9 times just before Write or Read command.

(2) Command Retry

Command retry is useful to recover from failure response during I²C communication.

■ ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Rating		Unit
		Min	Max	
Power supply voltage*	V_{DD}	– 0.5	+6.0	V
Input voltage*	V_{IN}	– 0.5	V_{DD} + 0.5 (≤ 6.0)	V
Output voltage*	V_{OUT}	– 0.5	V_{DD} + 0.5 (≤ 6.0)	V
Operation ambient temperature	T_A	– 40	+ 85	°C
Storage temperature	Tstg	– 55	+ 125	°C

*: These parameters are based on the condition that VSS is 0 V.

WARNING: Semiconductor devices can be permanently damaged by application of stress (voltage, current, temperature, etc.) in excess of absolute maximum ratings. Do not exceed these ratings.

■ RECOMMENDED OPERATING CONDITIONS

Parameter	Symbol	Value			Unit
		Min	Typ	Max	
Power supply voltage*	V_{DD}	3.0	—	5.5	V
“H” level input voltage*	V_{IH}	$V_{DD} \times 0.8$	—	5.5	V
“L” level input voltage*	V_{IL}	V_{SS}	—	$V_{DD} \times 0.2$	V
Operation ambient temperature	T_A	– 40	—	+ 85	°C

*: These parameters are based on the condition that VSS is 0 V.

WARNING: The recommended operating conditions are required in order to ensure the normal operation of the semiconductor device. All of the device's electrical characteristics are warranted when the device is operated within these ranges.

Always use semiconductor devices within their recommended operating condition ranges. Operation outside these ranges may adversely affect reliability and could result in device failure.

No warranty is made with respect to uses, operating conditions, or combinations not represented on the data sheet. Users considering application outside the listed conditions are advised to contact their representatives beforehand.

■ ELECTRICAL CHARACTERISTICS

1. DC Characteristics

(within recommended operating conditions)

Parameter	Symbol	Condition	Value			Unit
			Min	Typ	Max	
Input leakage current*1	$\|I_{LI}\|$	V_{IN} = 0 V to V_{DD}	—	—	1	µA
Output leakage current*2	$\|I_{LO}\|$	V_{OUT} = 0 V to V_{DD}	—	—	1	µA
Operating power supply current	I_{DD}	SCL = 400 kHz	—	40	80	µA
		SCL = 1000 kHz	—	90	130	µA
Standby current	I_{SB}	SCL, SDA = V_{DD} WP = 0 V or V_{DD} or Open Under Stop Condition T_A = + 25 °C	—	5	10	µA
“L” level output voltage	V_{OL}	I_{OL} = 3 mA	—	—	0.4	V
Input resistance for WP, A1, and A2 pins	R_{IN}	V_{IN} = V_{IL} (Max)	50	—	—	kΩ
		V_{IN} = V_{IH} (Min)	1	—	—	MΩ

*1: Applicable pin: SCL,SDA

*2: Applicable pin: SDA

2. AC Characteristics

Parameter	Symbol	Value						Unit
		STANDARD MODE		FAST MODE		FAST MODE PLUS		
		Min	Max	Min	Max	Min	Max	
SCL clock frequency	FSCL	0	100	0	400	0	1000	kHz
Clock high time	T_{HIGH}	4000	—	600	—	400	—	ns
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SCL/SDA falling time	T_f	—	300	—	300	—	100	ns
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SDA input setup	$T_{SU:DAT}$	250	—	100	—	100	—	ns
SDA output hold	$T_{DH:DAT}$	0	—	0	—	0	—	ns
Stop condition setup	$T_{SU:STO}$	4000	—	600	—	250	—	ns
SDA output access after SCL falling	T_{AA}	—	3000	—	900	—	550	ns
Pre-charge time	T_{BUF}	4700	—	1300	—	500	—	ns
Noise suppression time (SCL and SDA)	T_{SP}	—	50	—	50	—	50	ns

AC characteristics were measured under the following measurement conditions.

- Power supply voltage : STANDARD MODE and FAST MODE 3.0 V to 5.5 V
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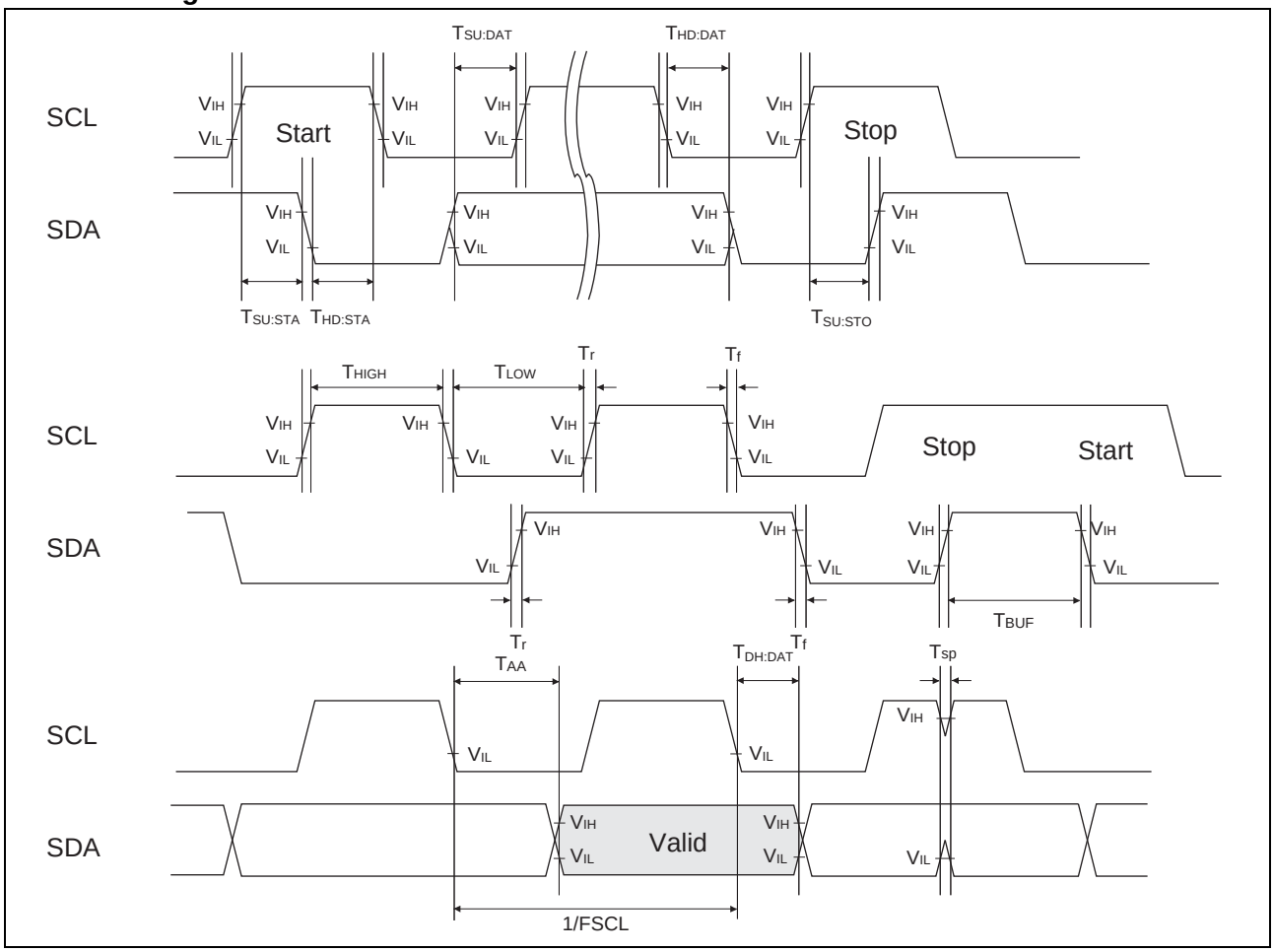

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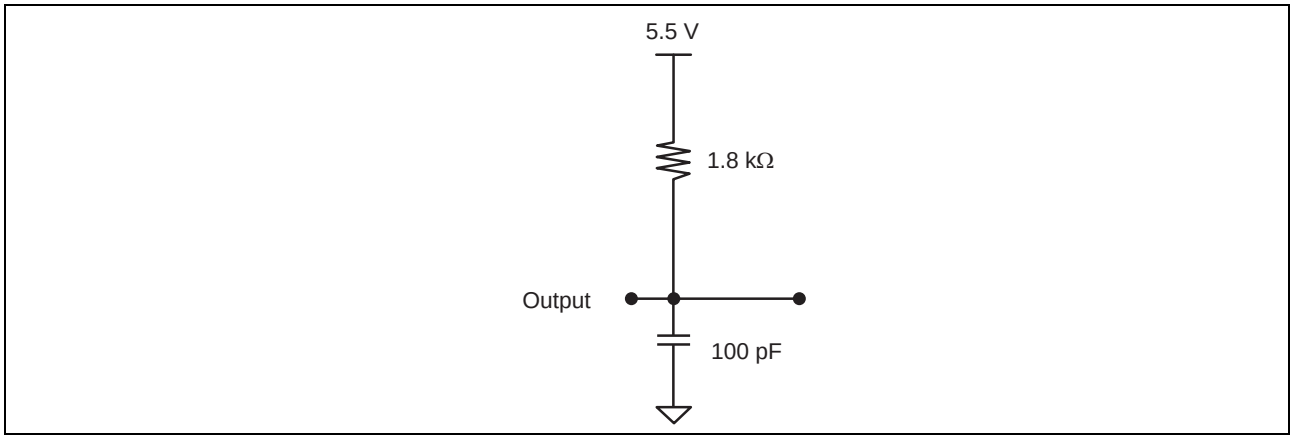
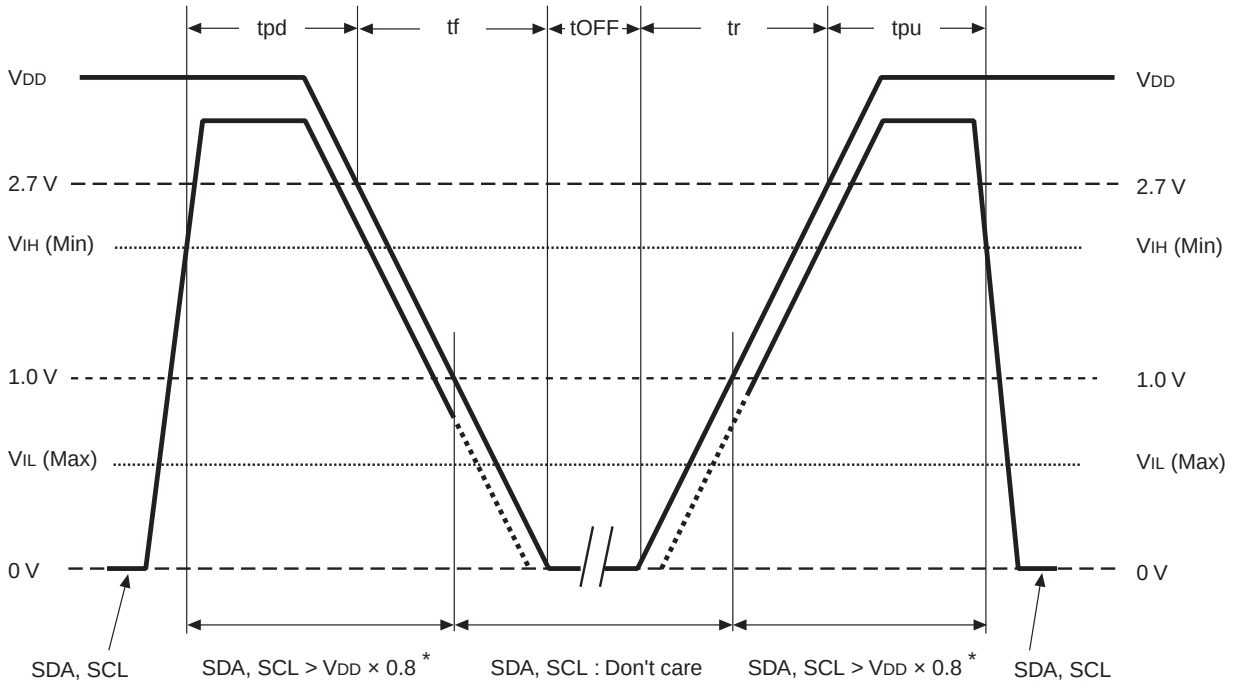
Parameter	Symbol	Conditions	Value			Unit
			Min	Typ	Max	
I/O capacitance	$C_{I/O}$	$V_{DD} = V_{IN} = V_{OUT} = 0$ V, f = 1 MHz, T_A = + 25 °C	—	—	15	pF
Input capacitance	C_{IN}		—	—	15	pF

5. AC Test Load Circuit



■ POWER ON SEQUENCE



* : SDA, SCL (Max) < V_{DD} + 0.5 V

Parameter	Symbol	Value		Unit
		Min	Max	
SDA, SCL level hold time during power down	tpd	85	—	ns
SDA, SCL level hold time during power up	tpu	85	—	ns
Power supply rising time	tr	0.5	50	ms
Power supply falling time	tf	0.5	50	ms
Power off time	tOFF	50	—	ms

If the device does not operate within the specified conditions of read cycle, write cycle or power on/off sequence, memory data can not be guaranteed.

■ FRAM CHARACTERISTICS

Item	Min	Max	Unit	Parameter
Read/Write Endurance*1	10^{12}	—	Times/byte	Operation Ambient Temperature T_A = + 85 °C
Data Retention*2	10	—	Years	Operation Ambient Temperature T_A = + 85 °C
	95	—		Operation Ambient Temperature T_A = + 55 °C
	≥ 200	—		Operation Ambient Temperature T_A = + 35 °C

*1 : Total number of reading and writing defines the minimum value of endurance, as an FRAM memory operates with destructive readout mechanism.

*2 : Minimun values define retention time of the first reading/writing data right after shipment, and these values are calculated by qualification results.

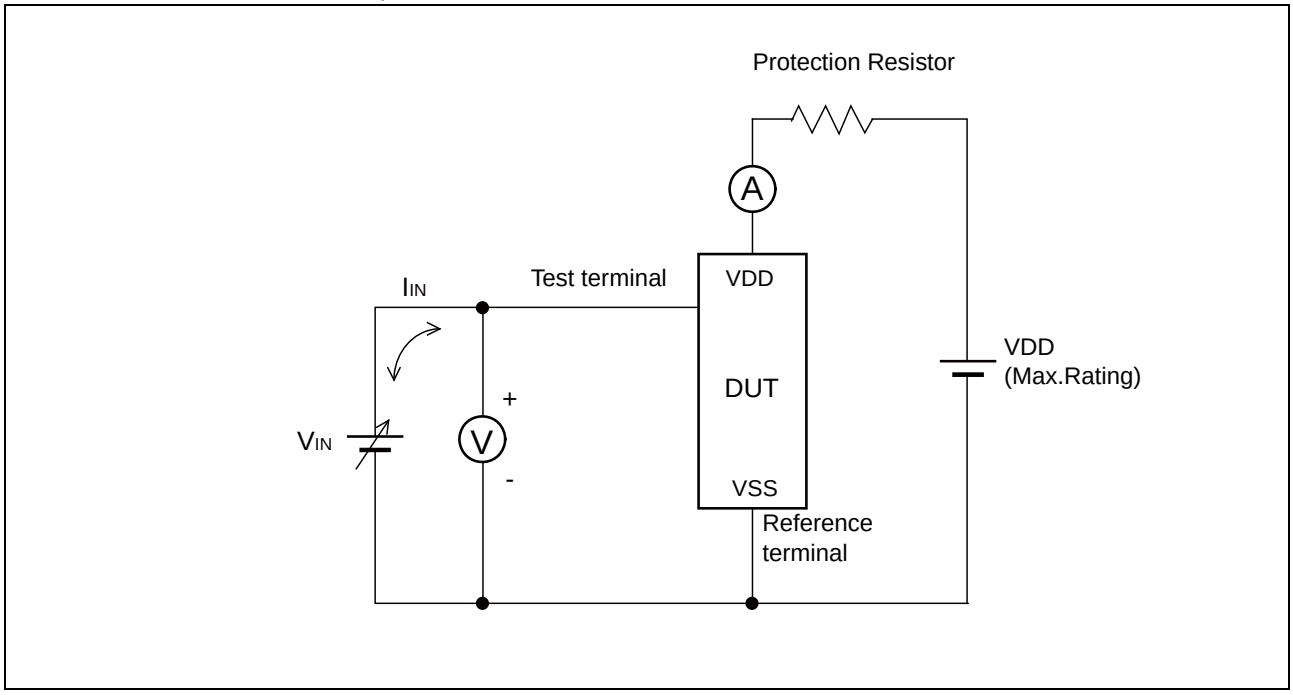
■ NOTE ON USE

- Data written before performing IR reflow is not guaranteed after IR reflow.
- During the access period from the start condition to the stop condition, keep the level of WP, A1, and A2 pins to the “H” level or the “L” level.

■ ESD AND LATCH-UP

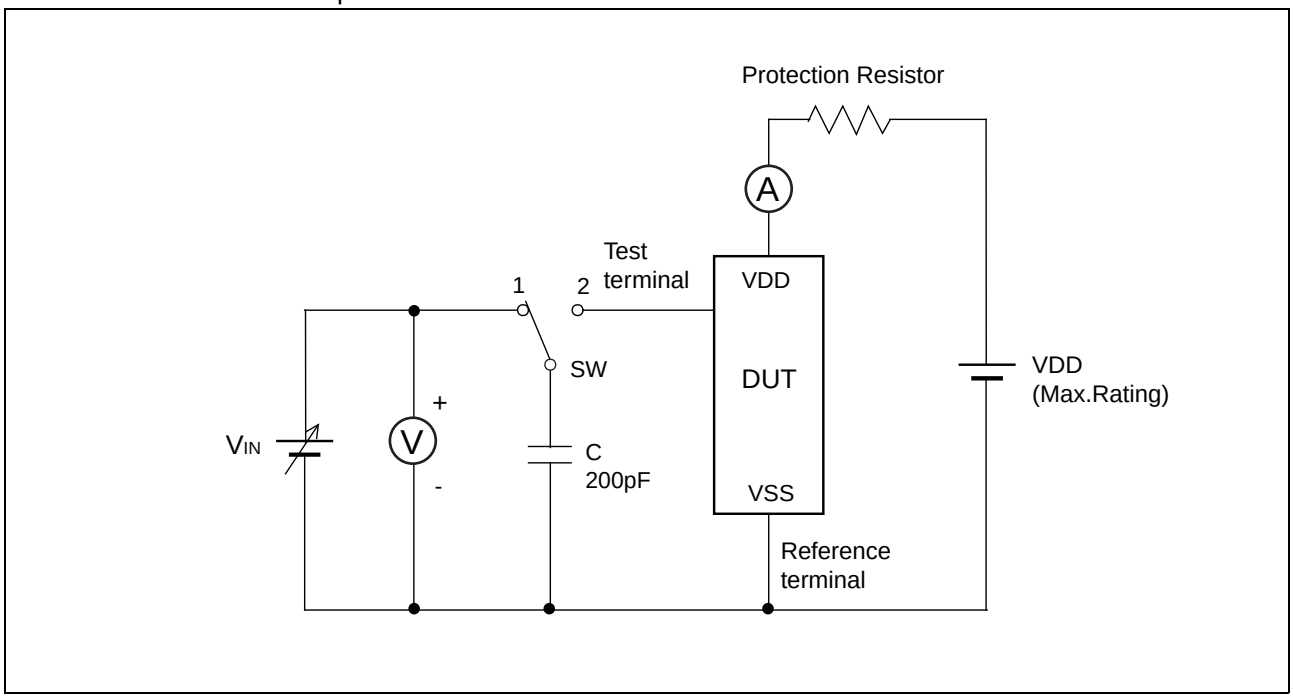
Test	DUT	Value
ESD HBM (Human Body Model) JESD22-A114 compliant	MB85RC04VPNF-G-JNE1	≥ |2000 V|
ESD MM (Machine Model) JESD22-A115 compliant		≥ |200 V|
ESD CDM (Charged Device Model) JESD22-C101 compliant		—
Latch-Up (I-test) JESD78 compliant		—
Latch-Up (V_{supply} overvoltage test) JESD78 compliant		—
Latch-Up (Current Method) Proprietary method		—
Latch-Up (C-V Method) Proprietary method		≥ |200 V|

- Current method of Latch-Up Resistance Test



Note : The voltage V_{IN} is increased gradually and the current I_{IN} of 300 mA at maximum shall flow. Confirm the latch up does not occur under $I_{IN} = \pm 300$ mA.
In case the specific requirement is specified for I/O and I_{IN} cannot be 300 mA, the voltage shall be increased to the level that meets the specific requirement.

• C-V method of Latch-Up Resistance Test

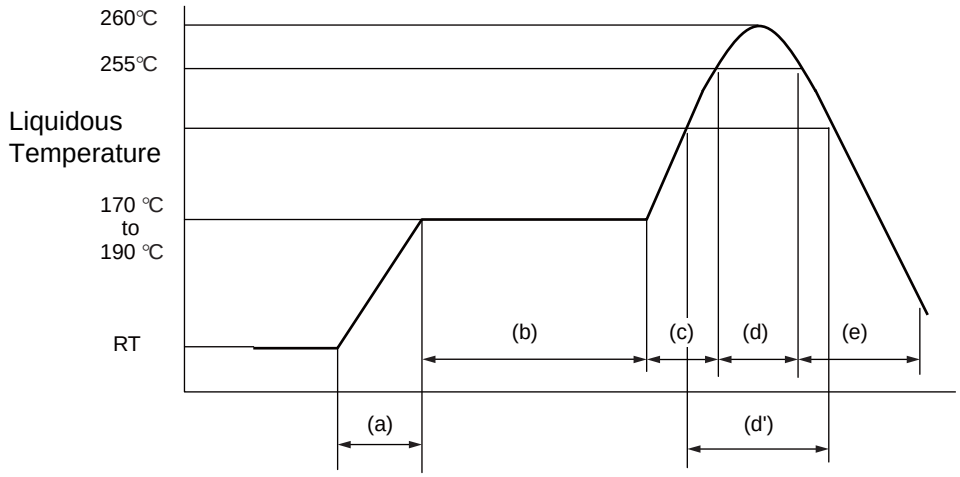


Note : Charge voltage alternately switching 1 and 2 approximately 2 sec interval. This switching process is considered as one cycle.
Repeat this process 5 times. However, if the latch-up condition occurs before completing 5times, this test must be stopped immediately.

■ REFLOW CONDITIONS AND FLOOR LIFE

Item	Condition	
Method	IR (infrared reflow) , Convection	
Times	2	
Floor life	Before unpacking	Please use within 2 years after production.
	From unpacking to 2nd reflow	Within 8 days
	In case over period of floor life	Baking with 125 °C+/-3 °C for 24hrs+2hrs/-0hrs is required. Then please use within 8 days. (Please remember baking is up to 2 times)
Floor life condition	Between 5 °C and 30 °C and also below 70%RH required. (It is preferred lower humidity in the required temp range.)	

Reflow Profile



(a) Average ramp-up rate : 1 °C/s to 4 °C/s
(b) Preheat & Soak : 170 °C to 190 °C, 60 s to 180 s
(c) Average ramp-up rate : 1 °C/s to 4 °C/s
(d) Peak temperature : Temperature 260 °C Max; 255 °C within 10 s
(d') Liquidous temperature : Up to 230 °C within 40 s or
Up to 225 °C within 60 s or
Up to 220 °C within 80 s
(e) Cooling : Natural cooling or forced cooling

Note : Temperature on the top of the package body is measured.

■ RESTRICTED SUBSTANCES

This product complies with the regulations below (Based on current knowledge as of November 2011).

- EU RoHS Directive (2002/95/EC)
- China RoHS (Administration on the Control of Pollution Caused by Electronic Information Products (电子信息产品污染控制管理办法))
- Vietnam RoHS (30/2011/TT-BCT)

Restricted substances in each regulation are as follows.

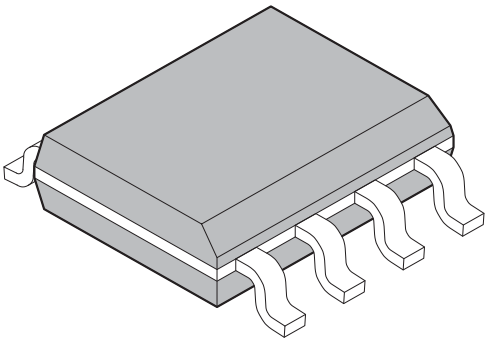
Substances	Threshold	Contain status*
Lead and its compounds	1,000 ppm	❍
Mercury and its compounds	1,000 ppm	❍
Cadmium and its compounds	100 ppm	❍
Hexavalent chromium compound	1,000 ppm	❍
Polybrominated biphenyls (PBB)	1,000 ppm	❍
Polybrominated diphenyl ethers (PBDE)	1,000 ppm	❍

* : The mark of "❍" shows below a threshold value.

■ ORDERING INFORMATION

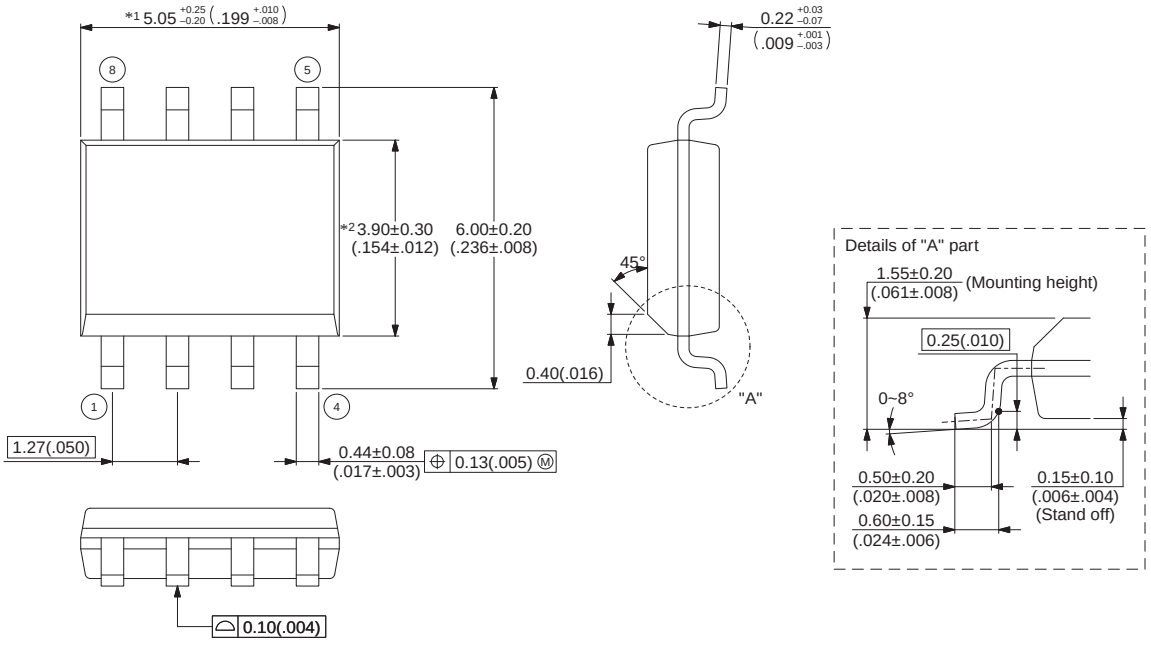
Part number	Package	Shipping form	Minimum shipping quantity
MB85RC04VPNF-G-JNE1	8-pin, plastic SOP (FPT-8P-M02)	Tube	1
MB85RC04VPNF-G-JNERE1	8-pin, plastic SOP (FPT-8P-M02)	Embossed Carrier tape	1500

■ PACKAGE DIMENSION

8-pin plastic SOP		
	Lead pitch	1.27 mm
	Package width × package length	3.9 mm × 5.05 mm
	Lead shape	Gullwing
	Sealing method	Plastic mold
	Mounting height	1.75 mm MAX
	Weight	0.06 g
(FPT-8P-M02)		

8-pin plastic SOP
(FPT-8P-M02)

Note 1) *1 : These dimensions include resin protrusion.
Note 2) *2 : These dimensions do not include resin protrusion.
Note 3) Pins width and pins thickness include plating thickness.
Note 4) Pins width do not include tie bar cutting remainder.



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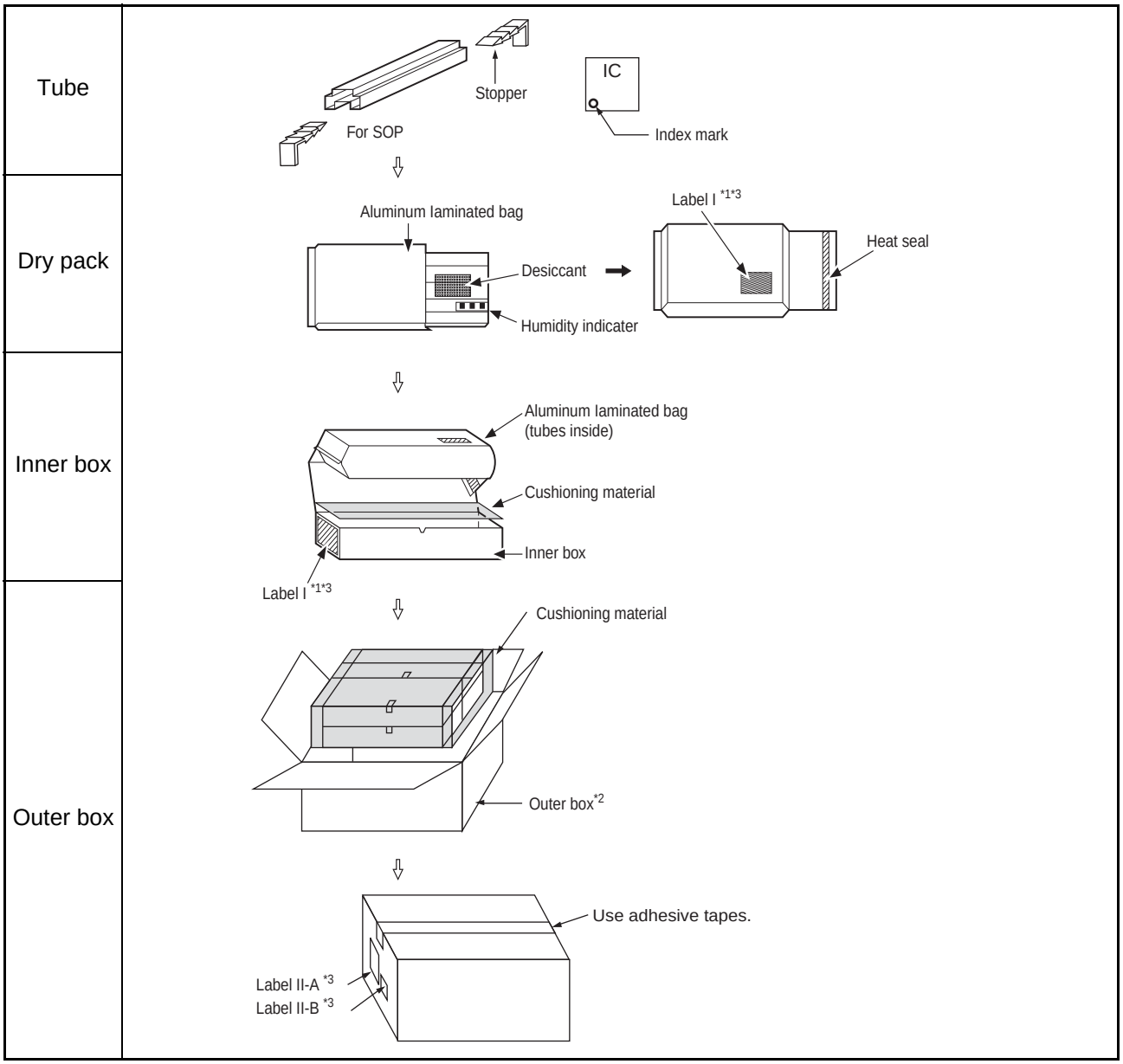
Dimensions in mm (inches).
Note: The values in parentheses are reference values.

Please check the latest package dimension at the following URL.
http://edevice.fujitsu.com/package/en-search/

1.2 Tube Dry pack packing specifications



*1: For a product of witch part number is suffixed with “E1”, a “ G Pb ” marks is display to the moisture barrier bag and the inner boxes.

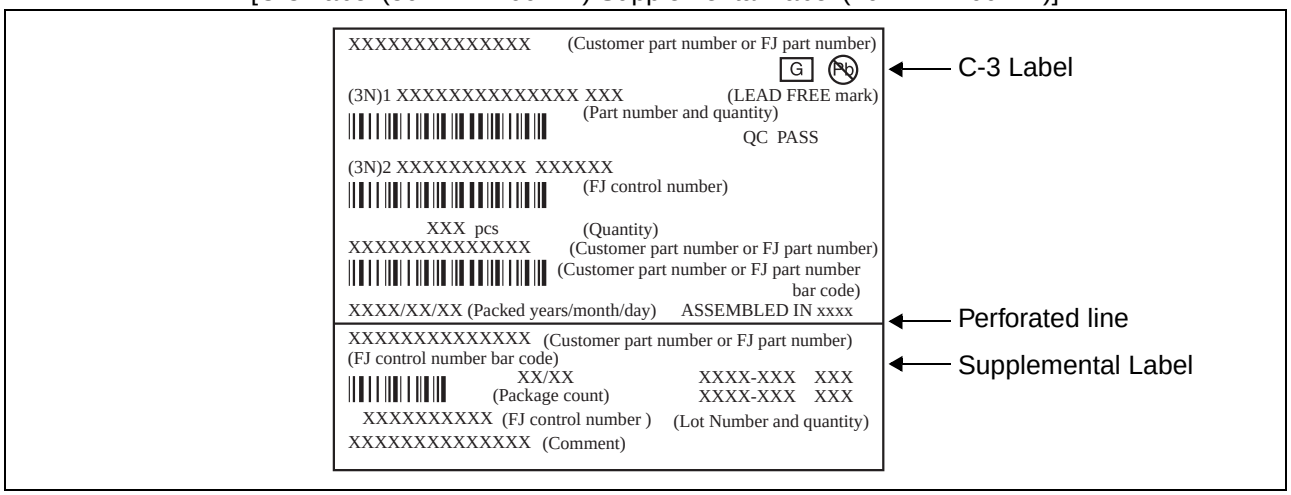
*2: The space in the outer box will be filled with empty inner boxes, or cushions, etc.

*3: Please refer to an attached sheet about the indication label.

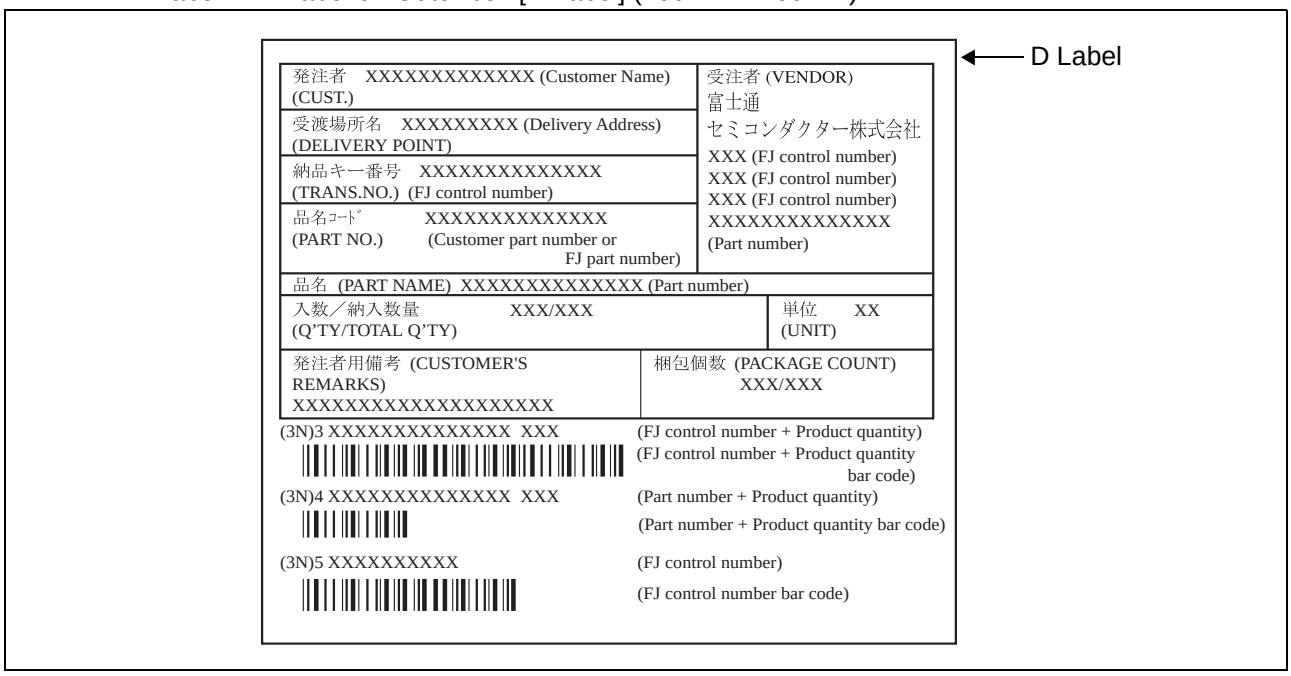
Note: The packing specifications may not be applied when the product is delivered via a distributer.

1.3 Product label indicators

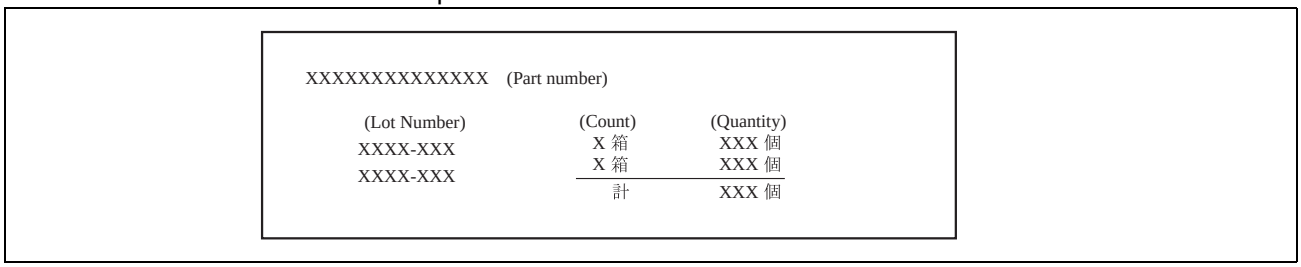
Label I: Label on Inner box/Moisture Barrier Bag/ (It sticks it on the reel for the emboss taping)
[C-3 Label (50mm × 100mm) Supplemental Label (20mm × 100mm)]



Label II-A: Label on Outer box [D Label] (100mm × 100mm)



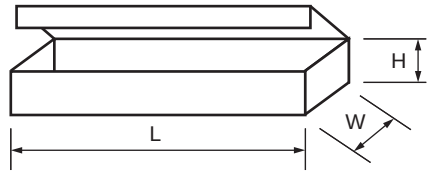
Label II-B: Outer boxes product indicate



Note: Depending on shipment state, “Label II-A” and “Label II-B” on the external boxes might not be printed.

1.4 Dimensions for Containers

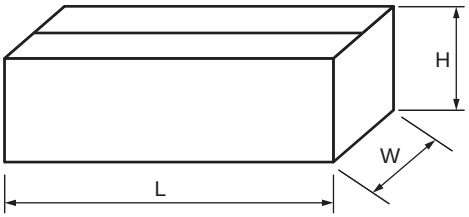
(1) Dimensions for inner box



L	W	H
540	125	75

(Dimensions in mm)

(2) Dimensions for outer box



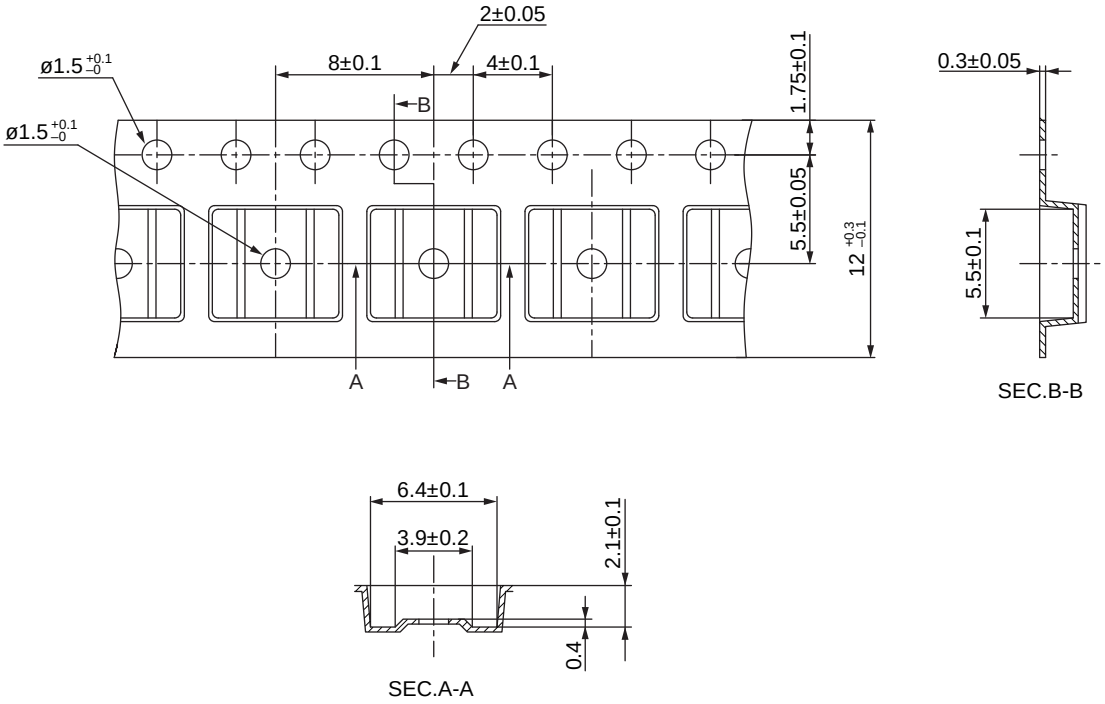
L	W	H
565	270	180

(Dimensions in mm)

2. Emboss Tape

2.1 Tape Dimensions

PKG code	Reel No	Maximum storage capacity		
		pcs/reel	pcs/inner box	pcs/outer box
FPT-8P-M02	3	1500	1500	10500



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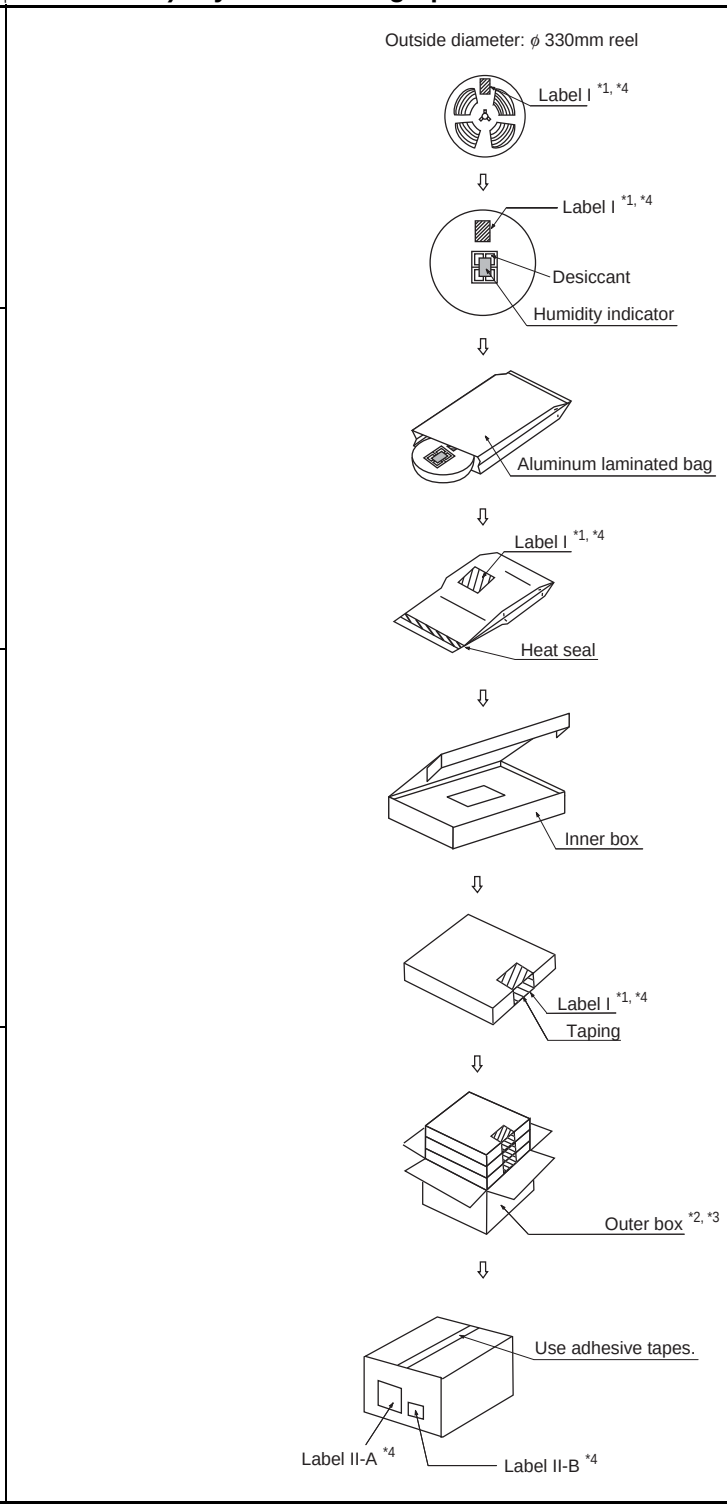
(Dimensions in mm)

Material : Conductive polystyrene
Heat proof temperature : No heat resistance.
Package should not be baked by using tape and reel.

2.4 Taping (ϕ330mm Reel) Dry Pack Packing Specifications

Embossed tapes	
Dry pack	
Inner box	
Outer box	

*1: For a product of witch part number is suffixed with “E1”, a “ G Pb ” marks is display to the moisture barrier bag and the inner boxes.

*2: The size of the outer box may be changed depending on the quantity of inner boxes.

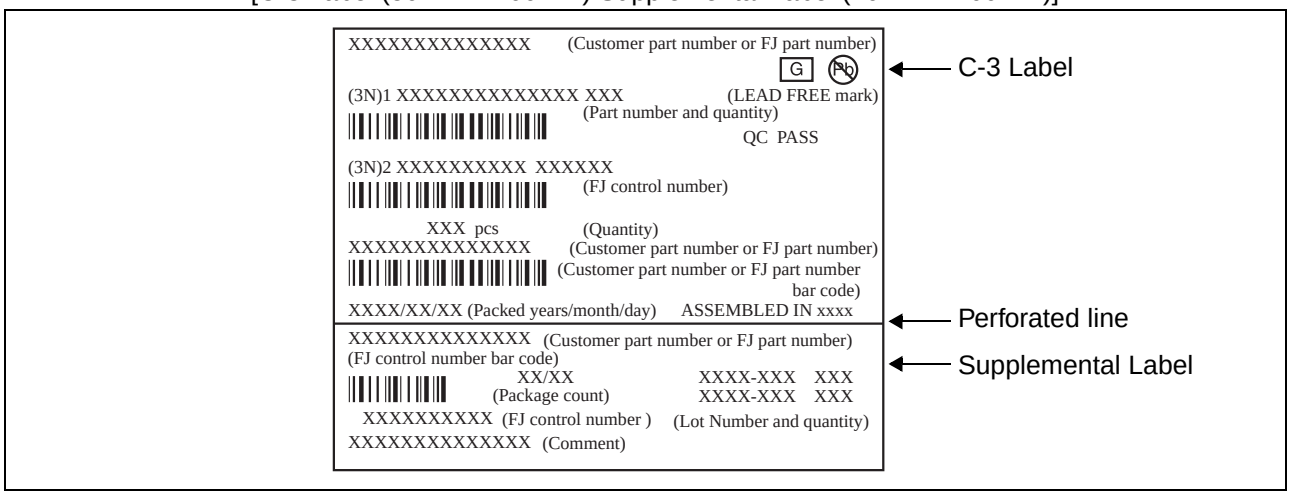
*3: The space in the outer box will be filled with empty inner boxes, or cushions, etc.

*4: Please refer to an attached sheet about the indication label.

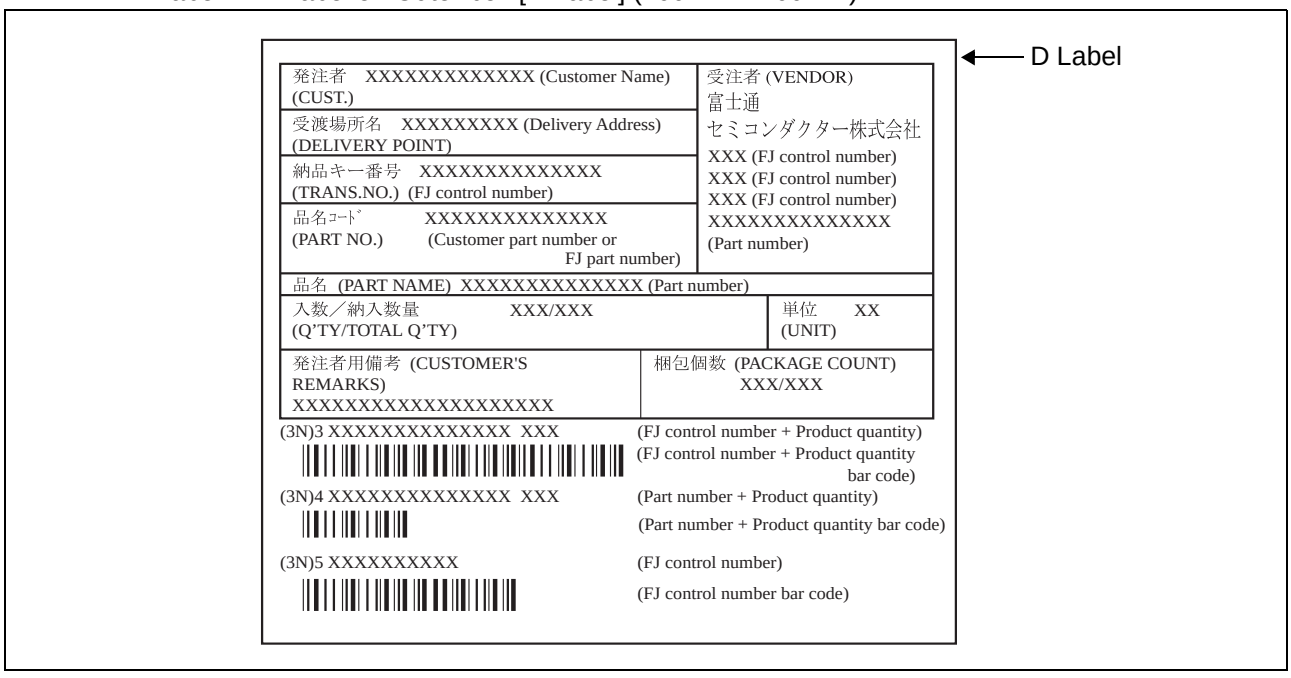
Note: The packing specifications may not be applied when the product is delivered via a distributer.

2.5 Product label indicators

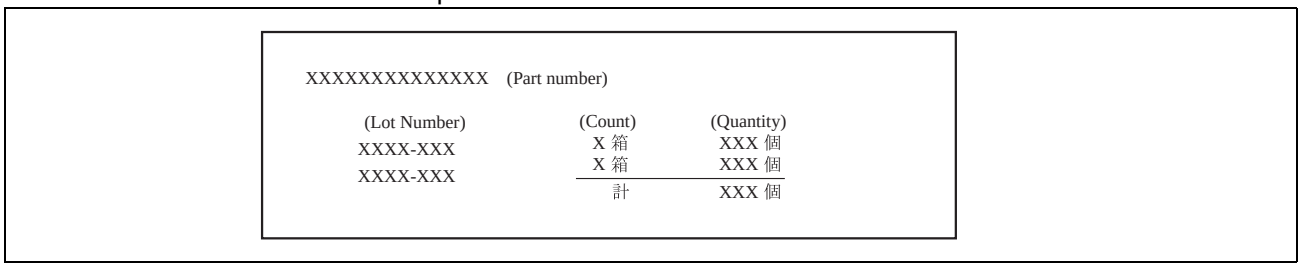
Label I: Label on Inner box/Moisture Barrier Bag/ (It sticks it on the reel for the emboss taping)
[C-3 Label (50mm × 100mm) Supplemental Label (20mm × 100mm)]



Label II-A: Label on Outer box [D Label] (100mm × 100mm)



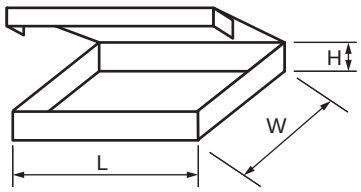
Label II-B: Outer boxes product indicate



Note: Depending on shipment state, “Label II-A” and “Label II-B” on the external boxes might not be printed.

2.6 Dimensions for Containers

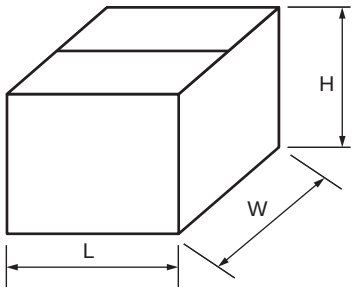
(1) Dimensions for inner box



Tape width	L	W	H
12, 16	365	345	40
24, 32			50
44			65
56			75

(Dimensions in mm)

(2) Dimensions for outer box



L	W	H
415	400	315

(Dimensions in mm)